

PBSS4240X

40 V, 2 A NPN low V_{CEsat} (BISS) transistor

15 October 2012

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS5240X.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High efficiency due to less heat generation

1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	40	V
I_C	collector current		-	-	2	A
I_{CM}	peak collector current		-	-	3	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1\text{ A}$; $I_B = 100\text{ mA}$; pulsed; $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	260	m Ω
I_{CRM}	repetitive peak collector current	$t_p \leq 20\text{ ms}$; $\delta \leq 0.33$; pulsed	-	-	2.5	A

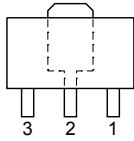
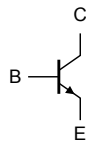


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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 <p style="text-align: center;">SOT89</p>	 <p style="text-align: center;"><i>sym123</i></p>
2	C	collector		
3	B	base		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS4240X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4240X	S47

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	40	V
V_{CEO}	collector-emitter voltage	open base	-	40	V
V_{EBO}	emitter-base voltage	open collector	-	5	V
I_C	collector current		-	2	A
I_{CRM}	repetitive peak collector current	$\delta \leq 0.33$; $t_p \leq 20$ ms; pulsed	-	2.5	A
I_{CM}	peak collector current		-	3	A
I_B	base current		-	300	mA
I_{BM}	peak base current		-	1	A
P_{tot}	total power dissipation	[1]	-	0.5	W
		[2]	-	0.95	W

Symbol	Parameter	Conditions		Min	Max	Unit
			[3]	-	1.35	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-65	150	°C
T_{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

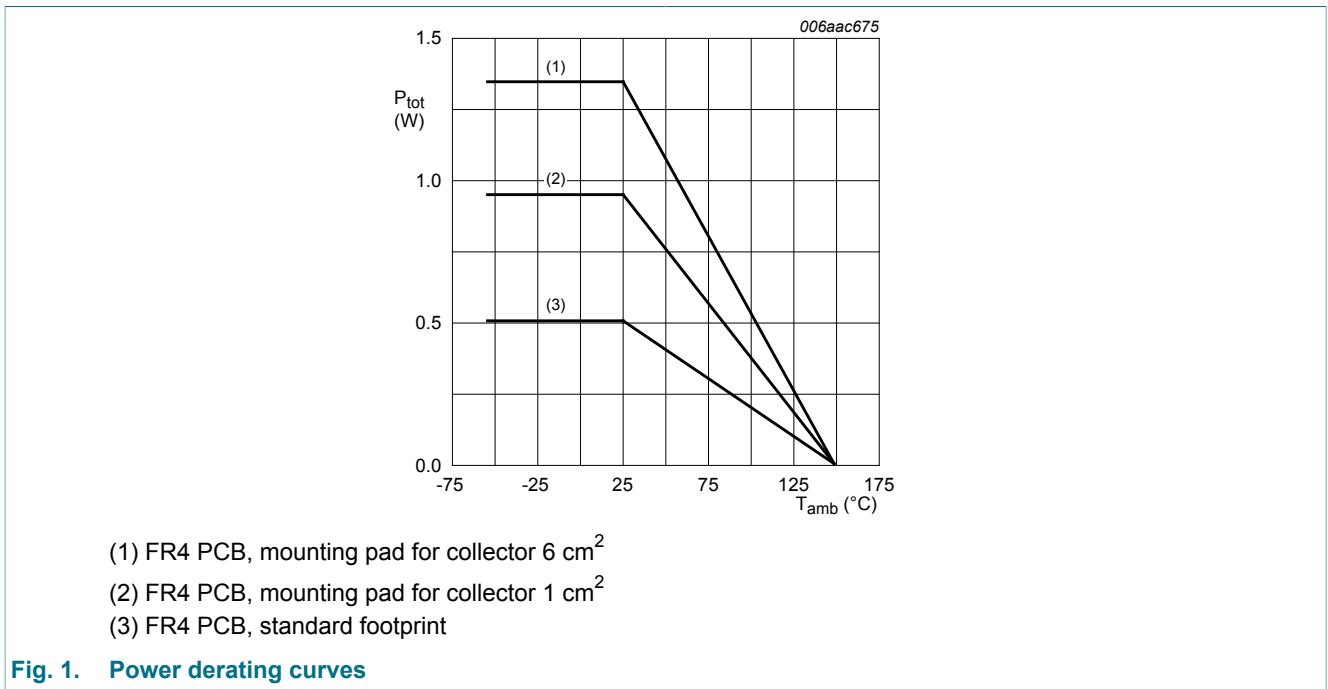


Fig. 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	132	K/W
			[3]	-	-	93	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

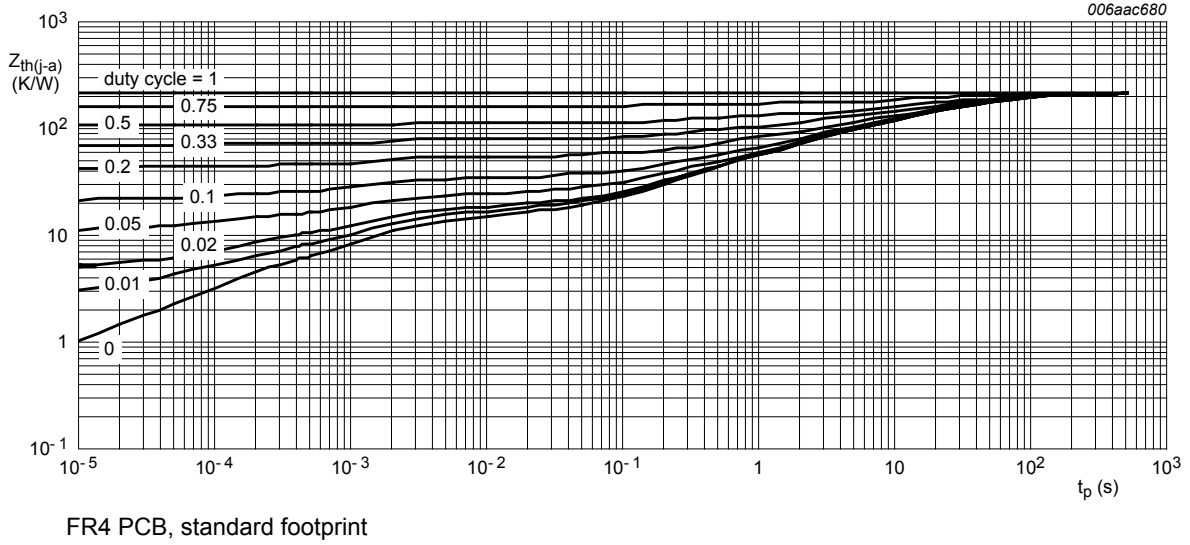


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

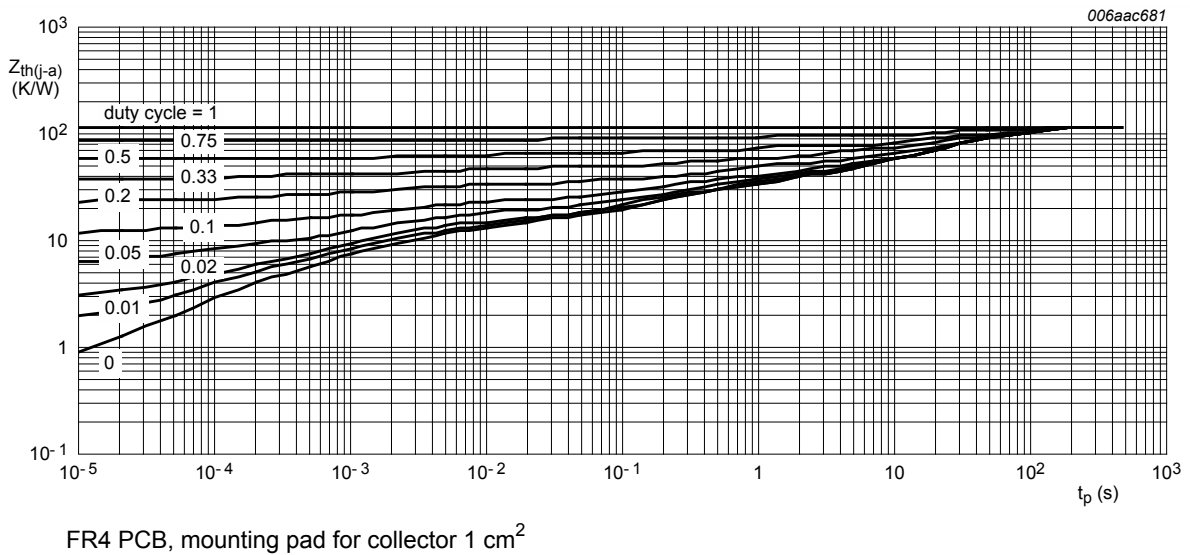
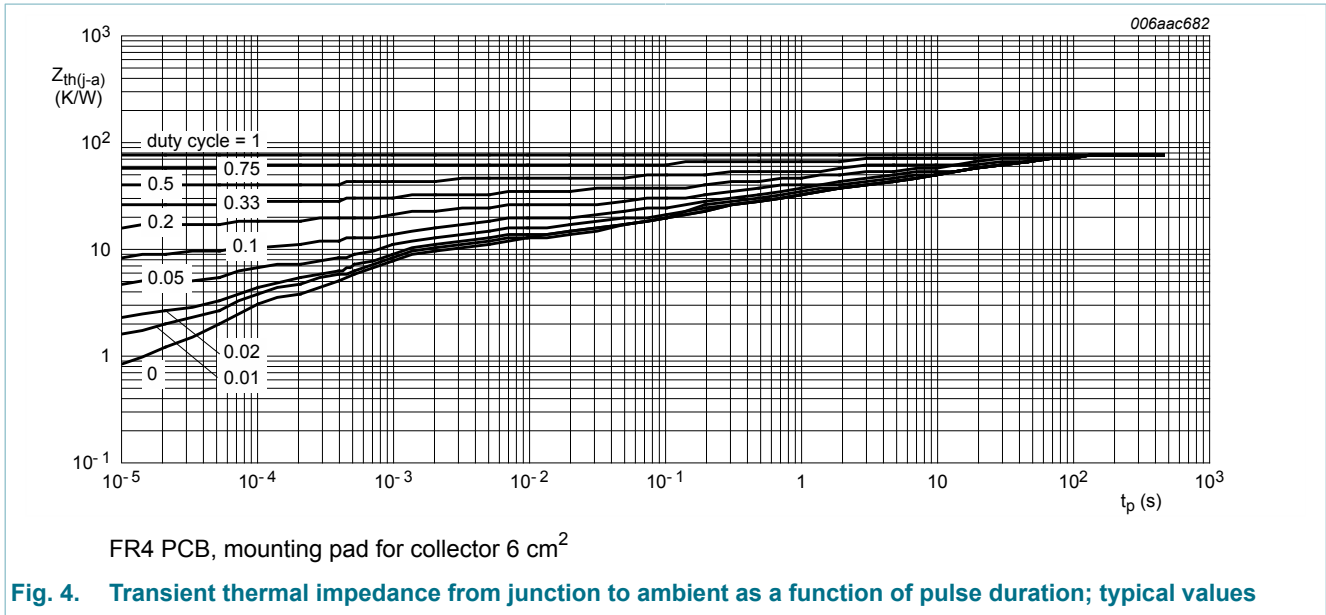


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = 40 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
		V _{CB} = 40 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	300	-	-	
		V _{CE} = 5 V; I _C = 500 mA; T _{amb} = 25 °C	300	-	900	
		V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	200	-	-	
		V _{CE} = 5 V; I _C = 2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	75	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	-	80	mV
		I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	140	mV
		I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	260	mV
		I _C = 2 A; I _B = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	510	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	260	mΩ

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}$; $I_B = 100\text{ mA}$; pulsed; $t_p \leq 300\ \mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}$; $I_C = 1\text{ A}$; pulsed; $t_p \leq 300\ \mu\text{s}$; $\delta \leq 0.02$; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	1.1	V
f_T	transition frequency	$V_{CE} = 10\text{ V}$; $I_C = 50\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	150	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}$; $I_E = 0\text{ A}$; $i_e = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	-	-	10	pF

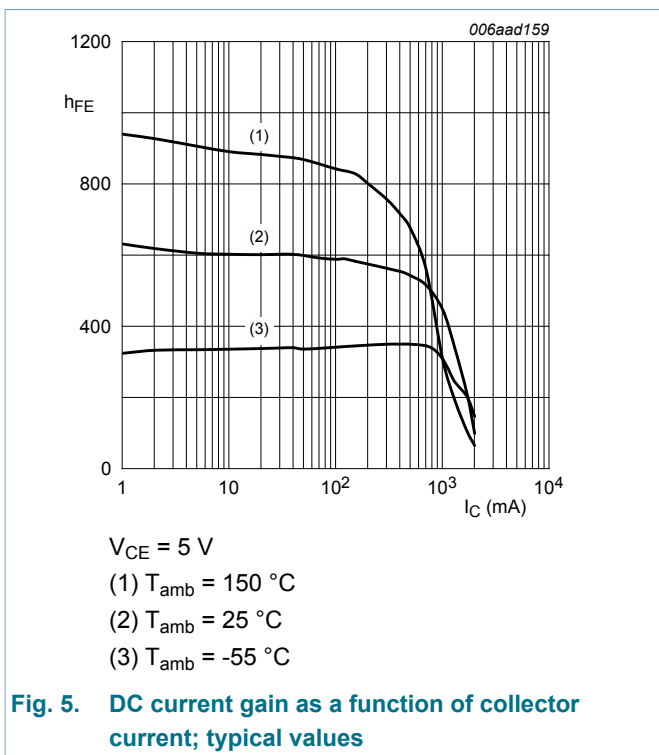


Fig. 5. DC current gain as a function of collector current; typical values

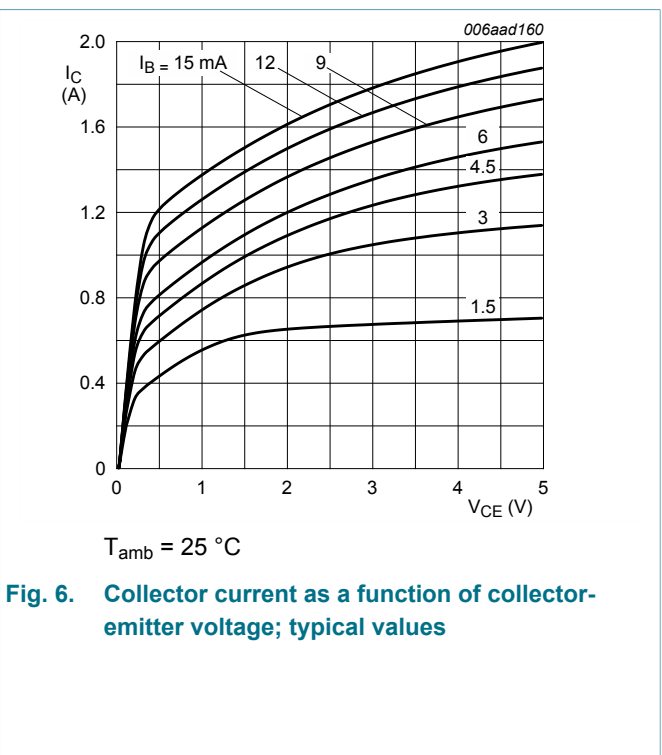
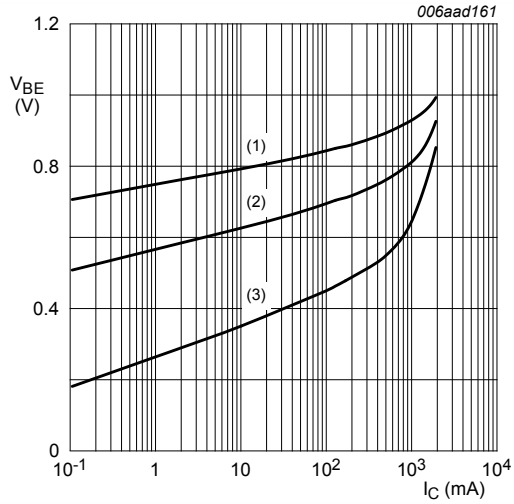
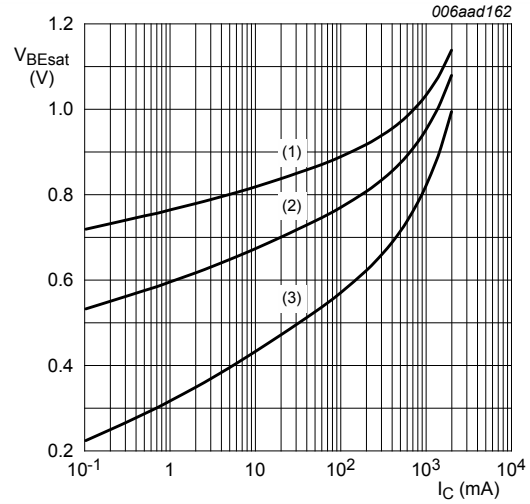


Fig. 6. Collector current as a function of collector-emitter voltage; typical values



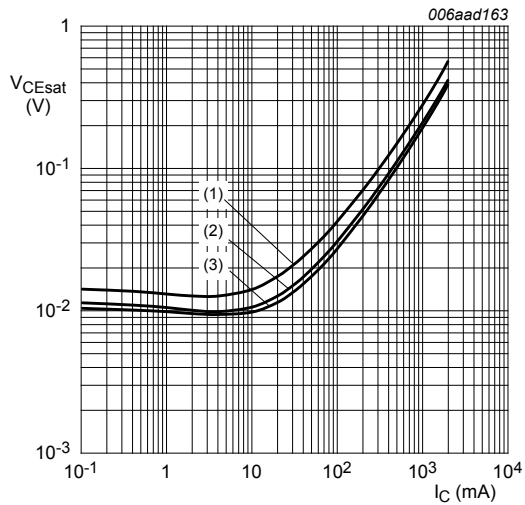
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



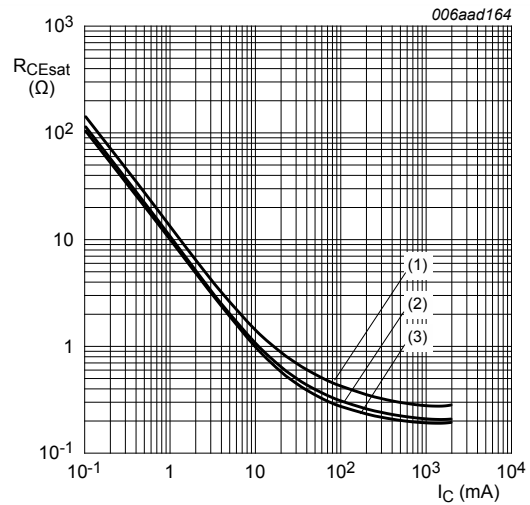
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

8. Package outline

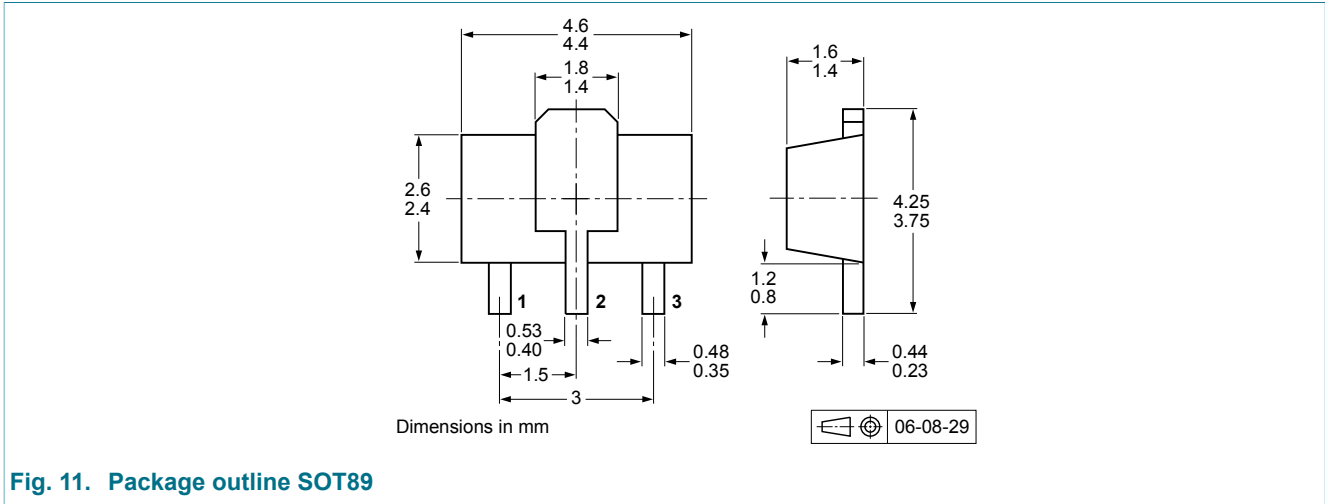


Fig. 11. Package outline SOT89

9. Soldering

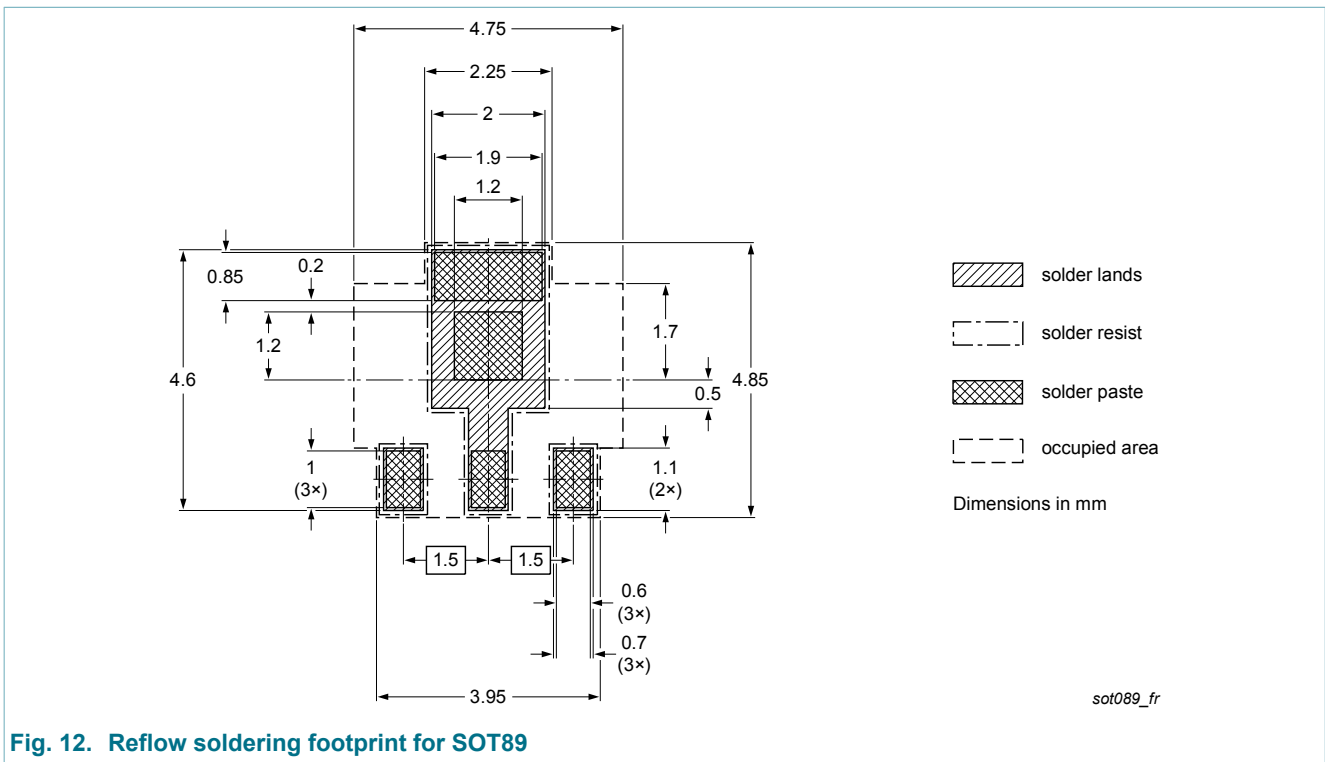


Fig. 12. Reflow soldering footprint for SOT89

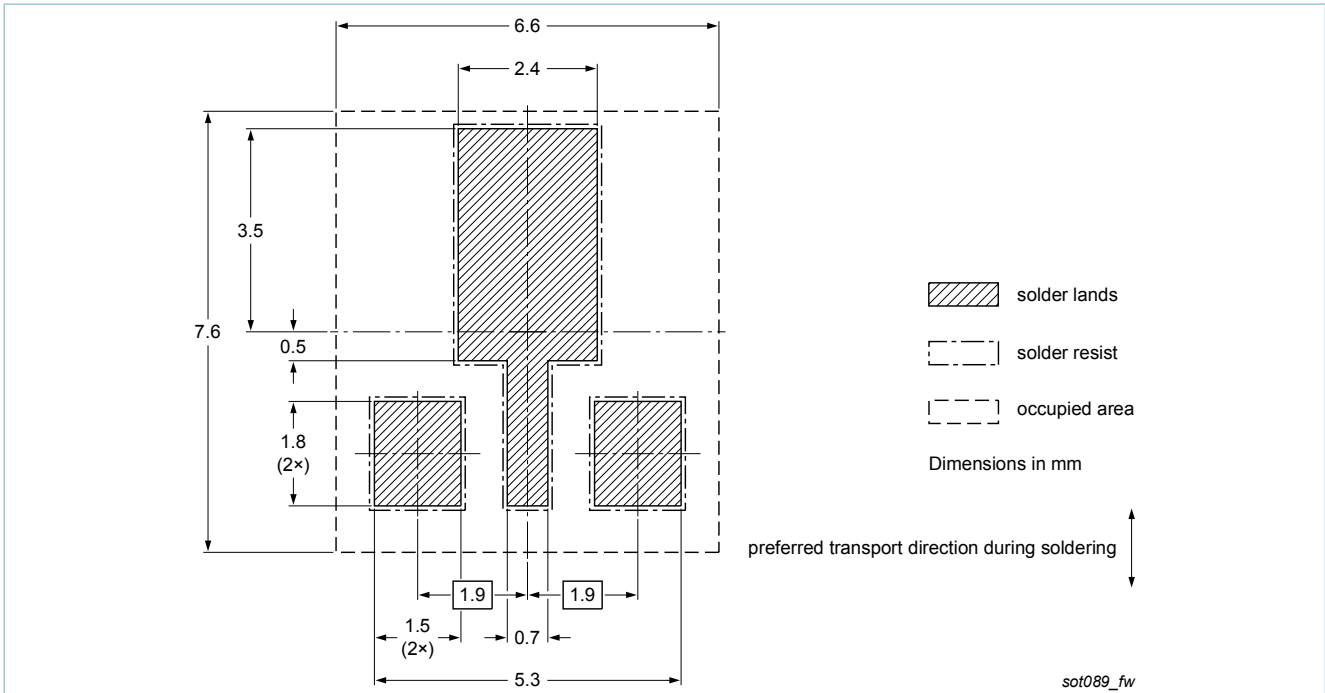


Fig. 13. Wave soldering footprint for SOT89

10. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4240X v.1	20121015	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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12. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	3
7	Characteristics	5
8	Package outline	8
9	Soldering	8
10	Revision history	9
11	Legal information	10
11.1	Data sheet status	10
11.2	Definitions	10
11.3	Disclaimers	10
11.4	Trademarks	11

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